

IN THE CLAIMS:

Please cancel claim 29, and amend claims 21, 27 and 31 as follows:

1-20. (Cancelled)

21. (Currently Amended) A method for depositing a metal-containing film to a substrate within a process chamber by an atomic layer deposition technique, comprising:

introducing a metal-containing precursor to the process chamber without a gaseous catalyst;

absorbing the metal-containing precursor to the substrate;

purging the process chamber with a purge gas;

introducing a process gas comprising a the metal-containing precursor and the gaseous catalyst;

reacting the absorbed metal-containing precursor with the process gas to deposit the metal-containing film; and

purging the process chamber with the purge gas.

22. (Previously Presented) The method of claim 21, wherein the metal-containing film comprises copper.

23. (Previously Presented) The method of claim 22, wherein the metal-containing precursor comprises a copper precursor.

24. (Previously Presented) The method of claim 23, wherein the copper precursor is copperhexafluoracetylacetonate trimethylvinylsilane.

25. (Previously Presented) The method of claim 23, wherein the gaseous catalyst comprises water.

26. (Previously Presented) The method of claim 25, wherein the purge gas is selected from the group consisting of argon, nitrogen, hydrogen and combinations thereof.

27. (Currently Amended) A method for depositing a copper-containing film to a substrate within a process chamber by an atomic layer deposition technique, comprising:

introducing a copper precursor to the process chamber;

absorbing the copper precursor to the substrate without a water catalyst;

purging the process chamber with a purge gas;

introducing a process gas comprising a gaseous the copper precursor and the water catalyst;

chemically reducing the absorbed copper precursor with the process gas to deposit the copper-containing film; and

purging the process chamber with the purge gas.

28. (Previously Presented) The method of claim 27, wherein the copper precursor is copperhexafluoracetylacetonate trimethylvinylsilane.

29. (Cancelled)

30. (Previously Presented) The method of claim 29, wherein the purge gas is selected from the group consisting of argon, nitrogen, hydrogen and combinations thereof.

31. (Currently Amended) A method for depositing a copper-containing film to a substrate within a process chamber by an atomic layer deposition technique, comprising:

introducing a copper precursor to the process chamber;

absorbing the copper precursor to the substrate;

purging the process chamber with a purge gas;

introducing a process gas comprising the copper precursor and water;

chemically reducing the absorbed precursor with the process gas to deposit the copper-containing film; and

purging the process chamber with the purge gas.

32. (Previously Presented) The method of claim 31, wherein the copper precursor is copperhexafluoracetylacetonate trimethylvinylsilane.